1		<del></del>		T	Total Times
Oxidation adj of adj silicon) or (framed adj local adj local adj oxidation adj of adj silicon) and (oxide near2 (layer or film) near5 (ion near2 implants4) near5 (oxygen near ion))) not (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon) same (oxide near2 (layer or film) near5 ((sion near2) near2 (layer or film)) same (through near5 (oxygen near ion)) same (through near5 (oxygen near ion)) same (through near5 (oxygen near ion)) near2 implants4) near5 (oxygen near ion)) near2 implants4) near5 (oxygen near ion)) near3 (438/42) or (438/423) or (438/423) or (438/434)	L Number	Hits	Search Text	DB	Time stamp
adj local adj oxidation adj of adj   silicon) and (oxide near2 (layer or film)   near5 ((ion near2 implant\$4) near5 (oxygen near ion))) not ((locas or (f adj locas) or (local adj oxidation adj of adj silicon) or (framed adj local) adj oxidation adj of adj silicon) or (framed adj local) adj oxidation adj of adj silicon) or (framed adj local) adj oxidation adj of adj silicon) or (framed adj local) adj oxidation adj of adj silicon) or (framed adj local) adj oxidation adj of adj silicon) or (framed)  - 7666 ((438/42) or (438/225) or (438/297) or USPAT; IBM TDB (438/438) or (438/436) or (438/434) or (438/434) or (438/439) or (438/436) or (438/434) or (438/439) or (438/436) or (438/434) or (438/439) or (438/436) or (438/43) or (438/439) or	1	41		1	2004/08/13 15:34
silicon) and (oxide near2 (layer or film)   near5 ((ion near2 implants4) near5 (oxygen near ion) )) not ((locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon) same (oxide near2 (layer or film) near5 ((ion near2 implants4) near5 (oxygen near ion))   same (through near5 (oxygen near ion))   same (through near5 (oxide near2 (layer or film))   Same (rithrough near5 (oxide near2 (layer or film))   Same (through near5 (oxide near2 (layer or film))   Same (through near5 (oxide near2 (layer or film))   Same (through near5 (oxide near2 (layer or film))   Same (rithrough near5 (rithrough near					
near5 ((ion near2 implant\$4) near5 (oxygen near ion))) not ((locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)) or (framed adj local adj oxidation adj of adj silicon)) same (oxide near2 (layer or film)) same ((ion near2 implant\$4) near5 (oxygen near ion)))   74					
near ion)   )) not ((locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon) same (oxide near2 (layer or film) near5 ((ion near2 implants4) near5 (oxygen near ion))   Same (nthrough near5 (oxygen near ion))   Same (through near5 (oxygen near ion))   Same (through near5 (oxygen near ion))   Same (through near5 (oxide near2 (layer or film))   Same ((ion near2 implants4) near5 (oxygen near ion))   Same (through near5 (oxygen near2 (layer or film))   Same ((ion near2 implants4) near5 (oxygen near2 (layer or film))   Same (ion)   Same					
or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon) or (framed adj local adj oxiden enar2 (layer or film) near5 ((lon near2 implants4) near5 (oxygen near ion) ))  74 oxide near2 (layer or film) same ((lon near2 implants4) near5 (oxygen near ion))  85 same (through near5 (oxygen near ion))  86 same (through near5 (oxygen near ion))  87 oxidation adj of adj silicon)  87				1511_155	
Silicon) or (framed adj local adj oxidation adj of adj silicon) same (oxide near2 (layer or film) near5 (in near2 implants4) near5 (oxygen near ion)   Oxide near2 (layer or film) same (((ion near2 inmplants4) near5 (oxygen near ion)   OSP-GFUB; BPO; JPO; DERWENT; IBM TDB (438/422) or (438/423) or (438/434) or (438/434) or (438/439) or (438/430) or (438/434) or (438/434) or (438/439) or (438/430) or (438/449) or (438/449) or (438/449) or (438/450) or (438/452) or (438/561) or (438/566) or (438/566) or (438/766) or (438					
near2 (layer or film) near5 ((ion near2 implants4) near5 (oxygen near ion) ))   oxide near2 (layer or film) same (((ion near2 implants4) near5 (oxygen near ion) or film))   same (through near5 (oxygen near ion)   SERWENT; IBM TDB (438/429) or (438/425) or (438/423) or USPAT; USPA			oxidation adj of adj silicon)) same (oxide		
1					
2   74					
	2	74	oxide near2 (layer or film)) same (((ion	USPAT;	2004/08/13 15:40
Film )			near2 implant\$4) near5 (oxygen near ion))	US-PGPUB;	
Tobe			same (through near5 (oxide near2 (layer or	EPO; JPO;	
- 1066 ((438/42) or (438/225) or (438/297) or (438/291) or (438/43) or (438/44) or (438/44) or (438/45) or (438/45) or (438/551) or (438/551) or (438/551) or (438/551) or (438/765) or (438/770) or (438/750) or (438/770) or			film)))	1	
(438/298) or (438/362) or (438/423) or (38/344) or (438/446) or (438/444) or (438/444) or (438/444) or (438/444) or (438/444) or (438/444) or (438/445) or (438/447) or (438/444) or (438/456) or (438/465) or (438/561) or (548/561) or (548/561) or (548/561) or (548/561) or (548/561) or (548/561) or (438/421) or (438/431) or (438/431) or (438/441) or (438/431) or (438/431) or (438/441) or (438/561) or (438/5				_	
(438/426) or (438/434) or (438/444) or (438/449) or (438/440) or (438/449) or (438/445) or (438/445) or (438/449) or (438/450) or (438/452) or (438/524) or (438/561) or (438/561) or (438/769) or (43	-	7066		1	2004/08/12 14:40
(438/449) or (438/440) or (438/444) or (438/449) or (438/450) or (438/450) or (438/450) or (438/524) or (438/561) or (438/566) or (438/766) or (438/760) or (438/7701).CCLS. implant\$4 near5 (oxygen near2 ion\$1)				1	
(438/445) or (438/447) or (438/49) or (438/452) or (438/524) or (438/524) or (438/526) or (438/526) or (438/561) or (438/766) or (438/769) or (438					
(438/450) or (438/452) or (438/524) or (438/564) or (438/546) or (438/547) or (438/761) or (438/766) or (438/769) or (438/770)).CCLS. implant\$4 near\$2 (oxygen near\$2 ion\$1) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J					
(438/546) or (438/547) or (438/551) or (438/766) or (438/769) or (438/7701).CCLS. implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film))   US-PGPUB; EPG; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; USPAT; US-PGPUB; EPG; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPG; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; US-				TRW_LDB	
486			1 ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '		
- 486 implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film))  - 594 (soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3)  - 16042 locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)  - 2 (((implant\$4 near5 (oxygen near2 ion\$1) near5 (fully near2 deplet\$3))) and (soi or (silicon near2 (layer or film)) near5 (fully near2 deplet\$3)) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj oxidation adj of adj silicon)) and (((438/42) or (438/225) or (438/297) or (438/439) or (438/439) or (438/439) or (438/440) or (438/450) or (438/450) or (438/561) or (438/561) or (438/760) or (438/760) or (438/561) or (438/700).CCLS.)  - 6 ((implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film)) and ((soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon))  - 14 (implant\$4 near5 (oxygen near2 ion\$1) near5 (oxygen near2 ion\$1) locos or (f adj locos) or (local adj oxidation adj of adj silicon))  - 14 (implant\$4 near5 (oxygen near2 ion\$1) near5 (oxygen near2 ion\$1) locos or (f adj locos) or (local adj oxidation adj of adj silicon))  - 14 (implant\$4 near5 (oxygen near2 ion\$1) locos or (f adj locos) or (local adj oxidation adj of adj silicon))  - 15 (implant\$4 near5 (oxygen near2 ion\$1) locos or (f adj locos) or (local adj oxidation adj of adj silicon))  - 16 (implant\$4 near5 (oxygen near2 ion\$1) locos or (f adj locos) or (local adj oxidation adj of adj silicon))  - 17 (locos or (local adj oxidation adj of adj silicon))  - 18 (locos or (local adj oxidation))  - 19 (locos or (local adj oxidation)  - 10 (locos or (local adj oxidation)  - 10 (locos or (local adj oxidation)  - 11 (locos or (locos) or (local adj oxidation)  - 12 (					
	_	106		IISDAT.	2004/08/13 12:35
S94	-	400			2004/06/13 12:33
- 594 (soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3)  - 16042 locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon) or (gramed adj local adj oxidation adj of adj silicon)  - 2 (((implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film)) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) adj of adj silicon) adj of adj silicon) adj or (adj silicon			I HOUTTO (STITCOM MEGIZ (Tayer Of IIIM))	1	
S94				1	
S94					
(fully near2 deplet\$3)	_	594	(soi or (silicon near2 insulator)) near5		2004/08/12 16:26
Comparison		334		-	
DERWENT; IBM TDB (USPĀT; USPĀT); (ISM TDB (USPĀT; USPĀT); (ISM TDB (USPĀT); USPĀT); (ISM TDB (USPĀT); USPĀT); (ISM TDB (USPĀT); (ISPĀT); (	į		,		
TEM_TDB	. 1				
16042   locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)   USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; USPĀT; US-PGPUB; USPĀT; US-PGPUB; USPĀT; US-PGPUB; USPĀT; US-PGPUB; USPĀT; USPĀ				-	
Oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)	ı - İ	16042	locos or (f adj locos) or (local adj		2004/08/13 12:37
adj local adj oxidation adj of adj silicon)   EPO; JPO; DERWENT; IBM_TDB   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	l l			US-PGPUB;	
-	l l				
-   2			silicon)		
near10 (silicon near2 (layer or film))   and ((soi or (silicon near2 insulator))   near5 (fully near2 deplet\$3)) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)) and (((438/42) or (438/225) or (438/297) or (438/298) or (438/362) or (438/423) or (438/426) or (438/433) or (438/444) or (438/445) or (438/440) or (438/449) or (438/450) or (438/447) or (438/449) or (438/566) or (438/547) or (438/561) or (438/766) or (438/769) or (438/770)).CCLS.) ((implant\$4 near5 (oxygen near2 ion\$1) near5 (fully near2 deplet\$3)) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon))   (implant\$4 near5 (oxygen near2 ion\$1)   (implant\$4 near5	į l	_			
and ((soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon))) and ((((438/42) or (438/25) or (438/297) or (438/426) or (438/362) or (438/433) or (438/439) or (438/433) or (438/444) or (438/445) or (438/447) or (438/449) or (438/45) or (438/452) or (438/524) or (438/546) or (438/547) or (438/561) or (438/766) or (438/769) or (438/770)).CCLS.)  ((implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film)) and ((soi or (silicon near2 ion\$1)) near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)) (implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film))  JUSPAT;  14 (spat)  USPAT;  USPAT;  2004/08/12 14:  15 (spat)  16 (spat)  17 (spat)  18 (spat)  19 (spat)  19 (spat)  10 (spat)  10 (spat)  11 (spat)  12 (spat)  13 (spat)  14 (spat)  15 (spat)  16 (spat)  17 (spat)  18 (spat)  19 (spat)  19 (spat)  19 (spat)  19 (spat)  10 (spat)  11 (spat)  11 (spat)  12 (spat)  13 (spat)  14 (spat)  15 (spat)  16 (spat)  17 (spat)  18 (spat)  19 (spat)  19 (spat)  10 (spat)  10 (spat)  11 (spat)  11 (spat)  12 (spat)  13 (spat)  14 (spat)  15 (spat)  16 (spat)  17 (spat)  18 (spat)  18 (spat)  18 (spat)  18 (spat)  19 (s	-	2		· ·	2004/08/12 14:24
near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj oxidation adj of adj silicon))) and (((438/42) or (438/225) or (438/297) or (438/298) or (438/362) or (438/423) or (438/426) or (438/433) or (438/444) or (438/445) or (438/447) or (438/444) or (438/445) or (438/447) or (438/449) or (438/450) or (438/452) or (438/524) or (438/546) or (438/547) or (438/561) or (438/766) or (438/769) or (438/770)).CCLS.)  - 6 ((implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film)) USPAT; near10 (soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)) (implant\$4 near5 (oxygen near2 ion\$1) USPAT; near10 (silicon near2 (layer or film)) USPAT; USPAT; near10 (silicon near2 (layer or film)) USPAT; USPAT; USPAT; Near10 (silicon near2 (layer or film)) USPAT; USP					
or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)) and (((438/42) or (438/225) or (438/297) or (438/298) or (438/362) or (438/423) or (438/426) or (438/433) or (438/444) or (438/445) or (438/447) or (438/449) or (438/450) or (438/452) or (438/524) or (438/566) or (438/547) or (438/561) or (438/766) or (438/769) or (438/770)).CCLS.)  - 6 ((implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film)) near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon))  adj oxidation adj of adj silicon))  (implant\$4 near5 (oxygen near2 ion\$1) to (implant\$4 near5 (oxygen near2) ton\$1 to (be the bottom adj oxidation adj of adj silicon))  (implant\$4 near5 (oxygen near2 ion\$1) to (implant\$4 near5 (oxygen near2) ton\$1 to USPAT; to (be the bottom adj oxidation adj of adj silicon))  (implant\$4 near5 (oxygen near2 ion\$1) to (implant\$4 near5 (oxygen near2) ton\$1 to USPAT; to (be the bottom adj oxidation adj of adj silicon))  (implant\$4 near5 (oxygen near2 ion\$1) to (implant\$4 near5 (oxygen near2) ton\$1 to USPAT; to (be the bottom adj oxidation adj oxidation adj oxidation adj oxidation)	1	*			
adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)) and (((438/42) or (438/225) or (438/297) or (438/298) or (438/362) or (438/423) or (438/426) or (438/434) or (438/439) or (438/440) or (438/444) or (438/445) or (438/447) or (438/449) or (438/450) or (438/452) or (438/524) or (438/546) or (438/547) or (438/561) or (438/766) or (438/769) or (438/770)).CCLS.)  - 6 ((implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film)) near5 (fully near2 deplet\$3)) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon)) (implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 insulator) (silicon near2 insulator) (silicon near2 insulator)) (silicon near2 insulator) (silicon)) (silicon) (silicon)) (silicon) (silicon)) (silicon) (silicon)) (silicon) (silicon) (silicon)) (silicon near2 (layer or film)) (silicon) (silicon near2 (layer or film)) (silicon) (silicon near2 (layer or film))) (silicon) (silicon near2 (layer or film))) (silicon) (silic				1	
adj oxidation adj of adj silicon))) and (((438/42) or (438/225) or (438/297) or (438/298) or (438/362) or (438/423) or (438/426) or (438/433) or (438/434) or (438/439) or (438/440) or (438/444) or (438/445) or (438/447) or (438/449) or (438/546) or (438/547) or (438/524) or (438/766) or (438/769) or (438/770)).CCLS.)  6 ((implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film)) us-PGPUB; and ((soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon))  14 (implant\$4 near5 (oxygen near2 ion\$1) usPAT; (implant\$4 near5 (oxygen near2) uspan u	, 1			TDM_TDB	
(((438/42) or (438/225) or (438/297) or (438/298) or (438/362) or (438/423) or (438/426) or (438/433) or (438/434) or (438/439) or (438/447) or (438/444) or (438/445) or (438/447) or (438/449) or (438/450) or (438/547) or (438/524) or (438/546) or (438/547) or (438/561) or (438/766) or (438/769) or (438/770)).CCLS.)  6 ((implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film)) yand (locos or (f adj locos) or (local adj oxidation adj of adj silicon))  or (f adj silicon) or (framed adj local adj oxidation adj of adj silicon))  (implant\$4 near5 (oxygen near2 ion\$1) USPAT; near10 (silicon near2 (layer or film)) yusPAT; USPAT; near10 (silicon near2 (layer or film)) yusPAT;	ı İ				
(438/298) or (438/362) or (438/423) or (438/426) or (438/433) or (438/434) or (438/439) or (438/440) or (438/444) or (438/445) or (438/447) or (438/449) or (438/50) or (438/524) or (438/546) or (438/547) or (438/561) or (438/766) or (438/769) or (438/770)).CCLS.)  6 ((implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film)) us-PGPUB; and ((soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3)) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)  14 (implant\$4 near5 (oxygen near2 ion\$1) usPAT; near10 (silicon near2 (layer or film)) usPAT; usPAT; near10 (silicon near2 (layer or film)) usPAT;					
(438/426) or (438/433) or (438/434) or (438/439) or (438/440) or (438/444) or (438/445) or (438/447) or (438/449) or (438/450) or (438/452) or (438/524) or (438/546) or (438/547) or (438/561) or (438/766) or (438/769) or (438/770)).CCLS.)  6 ((implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film)) us-PGPUB; and ((soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3))) and (locos or (fadj locos) or (local adj oxidation adj of adj silicon))  adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon))  (implant\$4 near5 (oxygen near2 ion\$1) usPAT; near10 (silicon near2 (layer or film))) usPAT; 2004/08/12 14:	<sub>i</sub> [				
(438/439) or (438/440) or (438/444) or (438/445) or (438/447) or (438/449) or (438/450) or (438/452) or (438/524) or (438/546) or (438/547) or (438/561) or (438/766) or (438/769) or (438/770)).CCLS.)  - ((implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film)) and ((soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon))  - (implant\$4 near5 (oxygen near2 ion\$1) USPAT; near10 (silicon near2 (layer or film))) USPAT; 2004/08/12 14:	<u> </u>				
(438/445) or (438/447) or (438/449) or (438/450) or (438/452) or (438/524) or (438/546) or (438/547) or (438/561) or (438/766) or (438/769) or (438/770)).CCLS.)  ((implant\$4 near5 (oxygen near2 ion\$1)					
(438/450) or (438/452) or (438/524) or (438/546) or (438/546) or (438/547) or (438/561) or (438/766) or (438/769) or (438/770)).CCLS.)  ((implant\$4 near5 (oxygen near2 ion\$1)	1	!			
(438/546) or (438/547) or (438/561) or (438/766) or (438/769) or (438/770)).CCLS.)  ((implant\$4 near5 (oxygen near2 ion\$1) USPAT; near10 (silicon near2 (layer or film)) US-PGPUB; and ((soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon))  (implant\$4 near5 (oxygen near2 ion\$1) USPAT; near10 (silicon near2 (layer or film))) US-PGPUB;	ļ				
(438/766) or (438/769) or (438/770)).CCLS.)  ((implant\$4 near5 (oxygen near2 ion\$1) uspat; near10 (silicon near2 (layer or film)) uspat; uspat; and ((soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon))  (implant\$4 near5 (oxygen near2 ion\$1) uspat; near10 (silicon near2 (layer or film)) uspat; uspat;					
(438/770)).CCLS.)  ((implant\$4 near5 (oxygen near2 ion\$1)					
- 6 ((implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film)) near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj oxidation adj of adj silicon))  - 14 (implant\$4 near5 (oxygen near2 ion\$1) near10 (silicon near2 (layer or film)) ) USPAT;	į l	i			
near10 (silicon near2 (layer or film)) ) and ((soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon))  (implant\$4 near5 (oxygen near2 ion\$1)	, -	6		USPAT;	2004/08/12 14:24
and ((soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon))  - 14 (implant\$4 near5 (oxygen near2 ion\$1) USPAT; near10 (silicon near2 (layer or film)) ) US-PGPUB;	,				
near5 (fully near2 deplet\$3))) and (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon))  14 (implant\$4 near5 (oxygen near2 ion\$1) USPAT; 2004/08/12 14:10 near10 (silicon near2 (layer or film)) US-PGPUB;	,				
or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon))  14 (implant\$4 near5 (oxygen near2 ion\$1) USPAT; 2004/08/12 14: near10 (silicon near2 (layer or film)) ) US-PGPUB;					
adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon))  14 (implant\$4 near5 (oxygen near2 ion\$1) USPAT; 2004/08/12 14: near10 (silicon near2 (layer or film)) ) US-PGPUB;	, ,				
adj oxidation adj of adj silicon))  - 14 (implant\$4 near5 (oxygen near2 ion\$1) USPAT; 2004/08/12 14: near10 (silicon near2 (layer or film)) ) US-PGPUB;				_	
near10 (silicon near2 (layer or film)) ) US-PGPUB;	.				
	-	14		USPAT;	2004/08/12 14:25
				ł	
			and ((soi or (silicon near2 insulator))	EPO; JPO;	
near5 (fully near2 deplet\$3)) DERWENT;			near5 (fully near2 deplet\$3))		
IBM_TDB				IBM_TDB	·

-9 -			T	10001/00/50 1: 55
	6	(implant\$4 near5 (oxygen near2 ion\$1)	USPAT;	2004/08/12 14:28
		near10 (silicon near2 (layer or film))	US-PGPUB;	
		same (trench\$2 or groove\$1 or open\$3 or	EPO; JPO;	1
		hole) ) and (((438/42) or (438/225) or	DERWENT;	
		(438/297) or (438/298) or (438/362) or	IBM TDB	ł
		(438/423) or (438/426) or (438/433) or	1201-122	
		(438/434) or (438/439) or (438/440) or		
		(438/444) or (438/445) or (438/447) or		
		(438/449) or (438/450) or (438/452) or		
}		(438/524) or (438/546) or (438/547) or		
		(438/561) or (438/766) or (438/769) or		
		(438/770)).CCLS.)		
-	47	implant\$4 near5 (oxygen near2 ion\$1)	USPAT;	2004/08/12 14:29
		near10 (silicon near2 (layer or film))	US-PGPUB;	
		same (trench\$2 or groove\$1 or open\$3 or	EPO; JPO;	
		hole)	DERWENT;	
		11016)	IBM TDB	
	-	/#4202001#   #4210054#   #4222417#	USPAT	2004/08/12 14:31
-	5	("4292091"   "4319954"   "4323417"	USPAT	2004/00/12 14:31
		"4338139"   "4339285").PN.		
-	20	4437225.URPN.	USPAT	2004/08/12 14:32
-	16		USPAT	2004/08/12 14:35
		"4810664"   "5032535"   "5114872"		
		"5279978"   "5418174"   "5460983"		
		"5482872"   "5527719"   "5610088"		
		"5612239"   "5612249"   "5712173"		
		"5733813").PN.		
_	11	,	USPAT	2004/08/12 14:37
		"5182226"   "5346841"   "5441094"		
		"5472902"   "5488004"   "5494846"		
		"5707899"   "5712186").PN.		
	107701	· · · · · · · · · · · · · · · · · · ·	HODAM.	2004/08/12 16:27
_	107731		USPAT;	2004/08/12 16:2/
		adj oxidation adj of adj silicon) or	US-PGPUB;	
		(framed adj local adj oxidation adj of adj	EPO; JPO;	
		silicon)or (field near2 oxide)	DERWENT;	
			IBM_TDB	
_	11	(((438/42) or (438/225) or (438/297) or	USPAT;	2004/08/12 14:41
		(438/298) or (438/362) or (438/423) or	US-PGPUB;	
		(438/426) or (438/433) or (438/434) or	EPO; JPO;	
		(438/439) or (438/440) or (438/444) or	DERWENT;	
		(438/445) or (438/447) or (438/449) or	IBM TDB	
		(438/450) or (438/452) or (438/524) or		
		(438/546) or (438/547) or (438/561) or	ŀ	
			<b>,</b>	
		(438/766) or (438/769) or		
		(438/770)).CCLS.) and ((implant\$4 near5		
		(oxygen near2 ion\$1) near10 (silicon near2		
		(layer or film)) ) and (locos or (f adj		
		locos) or (local adj oxidation adj of adj	1	
		silicon) or (framed adj local adj		
		oxidation adj of adj silicon)))		
_ [	62	(implant\$4 near5 (oxygen near2 ion\$1)	USPAT;	2004/08/12 14:54
	- 1	near10 (silicon near2 (layer or film)) )	US-PGPUB;	
		and (locos or (f adj locos) or (local adj	EPO; JPO;	
		oxidation adj of adj silicon) or (framed	DERWENT;	
				ļ
		adj local adj oxidation adj of adj	IBM_TDB	[
		silicon))	1	I .

				_
	51	((implant\$4 near5 (oxygen near2 ion\$1)	USPAT;	2004/08/12 14:44
		near10 (silicon near2 (layer or film)))	US-PGPUB;	
		and (locos or (f adj locos) or (local adj	EPO; JPO;	
		oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj	DERWENT;	1
		silicon))) not ((((438/42) or (438/225) or	IBM_TDB	
		(438/297) or (438/298) or (438/362) or		
İ		(438/423) or (438/426) or (438/433) or		
		(438/434) or (438/439) or (438/440) or		
		(438/444) or (438/445) or (438/447) or		
1		(438/449) or (438/450) or (438/452) or	ζ.	· N
		(438/524) or (438/546) or (438/547) or		
		(438/561) or (438/766) or (438/769) or		į'
		(438/770)).CCLS.) and ((implant\$4 near5		
		(oxygen near2 ion\$1) near10 (silicon near2		
		(layer or film)) ) and (locos or (f adj locos) or (local adj oxidation adj of adj		
		silicon) or (framed adj local adj		
		oxidation adj of adj silicon))))		
_	5		USPAT;	2004/08/12 14:53
		near10 (silicon near2 (layer or film)) )	US-PGPUB;	
		same (locos or (f adj locos) or (local adj	EPO; JPO;	
		oxidation adj of adj silicon) or (framed	DERWENT;	
		adj local adj oxidation adj of adj	IBM_TDB	
		silicon))		2004/00/10 14:55
_	12	((implant\$4 near5 (oxygen near2 ion\$1)	USPAT;	2004/08/12 14:56
		near10 (silicon near2 (layer or film))) same oxidiz\$5) and (locos or (f adj locos)	US-PGPUB; EPO; JPO;	
		or (local adj oxidation adj of adj	DERWENT;	
	İ	silicon) or (framed adj local adj	IBM TDB	
		oxidation adj of adj silicon))		
-	59	(implant\$4 near5 (oxygen near2 ion\$1)	USPAT;	2004/08/12 14:56
		near10 (silicon near2 (layer or film)))	US-PGPUB;	
		same oxidiz\$5	EPO; JPO;	
			DERWENT;	
	100	1 - 3 - 4 0 4 - 4 - 5 - 7 - 4 - 4 - 4 - 4 - 4 - 4 - 4 - 4 - 4	IBM_TDB	0004/00/10 16 06
-	486	implant\$4 near5 (oxygen near2 ion\$1)	USPAT;	2004/08/12 16:26
1		near10 (silicon near2 (layer or film))	US-PGPUB; EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
_	594	(soi or (silicon near2 insulator)) near5	USPĀT;	2004/08/12 16:27
		(fully near2 deplet\$3)	US-PGPUB;	·
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	107731	fox or locos or (f adj locos) or (local	USPAT;	2004/08/12 21:17
		adj oxidation adj of adj silicon) or	US-PGPUB;	
		(framed adj local adj oxidation adj of adj silicon)or (field near2 oxide)	EPO; JPO; DERWENT;	
İ		STITEON/OF (TIETO NEATZ OXIGE)	IBM TDB	
-	0	(implant\$4 near5 (oxygen near2 ion\$1)	USPAT;	2004/08/12 16:58
		near10 (silicon near2 (layer or film)) )	US-PGPUB;	= = = = = = = = = = = = = = = =
		<pre>same ((soi or (silicon near2 insulator))</pre>	EPO; JPO;	j
		near5 (fully near2 deplet\$3))	DERWENT;	İ
			IBM_TDB	
-	14	(implant\$4 near5 (oxygen near2 ion\$1)	USPAT;	2004/08/12 16:28
		near10 (silicon near2 (layer or film)))	US-PGPUB;	
		and ((soi or (silicon near2 insulator))	EPO; JPO;	
		near5 (fully near2 deplet\$3))	DERWENT; IBM TDB	[
_	6	("5955767"   "6100159"   "6174754"	USPAT	2004/08/12 16:32
		"6403433"   "6501133"   "6515333").PN.	302	
_	0	6724049.URPN.	USPAT	2004/08/12 16:33
-	1	6501133.URPN.	USPAT	2004/08/12 16:34
-	8	("5614729"   "5920097"   "5955767"	USPAT	2004/08/12 16:34
		"6100159"   "6130457"   "6174754"		
		"6287901"   "6303412").PN.		

r <u>' '</u>				
_	41	((soi or (silicon near2 insulator)) near5 (fully near2 deplet\$3)) same (fox or locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)or (field	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 16:58
-	107731	near2 oxide)) fox or locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)or (field near2 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/12 21:18
-	92	adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)or (field near2 oxide)) near10	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/08/12 21:45
-	18	(sidewall\$1 near trench\$2) (fox or locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon) or (field near2 oxide)) near10 ((etch\$3 near5 sidewall\$1) near3 trench\$2)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/12 21:46
_	995	oxide near2 (layer or film) same ((ion near2 implant\$4) near5 (oxygen near ion))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/13 15:37
-	. 16042	locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/13 12:37
_	15	(oxide near2 (layer or film) same ((ion near2 implant\$4) near5 (oxygen near ion) )) same (locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/13 12:37
_	325	oxide near2 (layer or film) near5 ((ion near2 implant\$4) near5 (oxygen near ion))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/13 15:36
-	49	(locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)) and (oxide near2 (layer or film) near5 ((ion near2 implant\$4) near5 (oxygen near ion)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/13 12:44
	8	(locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)) same (oxide near2 (layer or film) near5 ((ion near2 implant\$4) near5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/13 12:44
-	41	(oxygen near ion) )) ((locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)) and (oxide near2 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/08/13 15:33
		near5 ((ion near2 implant\$4) near5 (oxygen near ion) )) not ((locos or (f adj locos) or (local adj oxidation adj of adj silicon) or (framed adj local adj oxidation adj of adj silicon)) same (oxide near2 (layer or film) near5 ((ion near2	IBM_TDB	
	1	<pre>implant\$4) near5 (oxygen near ion) )))</pre>		

	276	(oxide near2 (layer or film) near5 ((ion	USPAT;	2004/08/13 12:52
-	270	near2 implant\$4) near5 (oxygen near ion)	US-PGPUB;	2004/00/13 12:32
		)) not ((locos or (f adj locos) or (local	EPO; JPO;	
		adj oxidation adj of adj silicon) or	DERWENT;	
1		(framed adj local adj oxidation adj of adj	IBM TDB	
1			1011-100	
		silicon)) and (oxide near2 (layer or film)		
1	İ	near5 ((ion near2 implant\$4) near5 (oxygen		
1		near ion))))		0004/00/12 10 50
-	0	1 ( ( ) ( ( ) ( )	USPAT;	2004/08/13 12:52
		near2 implant\$4) near5 (oxygen near ion)	US-PGPUB;	
		)) not ((locos or (f adj locos) or (local	EPO; JPO;	İ
		adj oxidation adj of adj silicon) or	DERWENT;	
		(framed adj local adj oxidation adj of adj	IBM_TDB	
		silicon)) and (oxide near2 (layer or film)		
		near5 ((ion near2 implant\$4) near5 (oxygen		1
		near ion) )))) and (locos or (f adj locos)		
	1	or (local adj oxidation adj of adj		
		silicon) or (framed adj local adj		
		oxidation adj of adj silicon))		